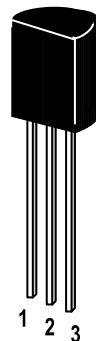


ST 1702

NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications



The transistor is subdivided into five groups, L, M, N, O and P, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.

1. Emitter 2. Base 3. Collector

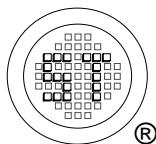
TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	30	V
Collector Emitter Voltage	V_{CEO}	25	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	1	A
Power Dissipation	P_{tot}	600	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_S	- 55 to + 150	°C

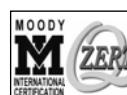
Characteristics at $T_{amb} = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 1 \text{ V}$, $I_C = 100 \text{ mA}$	h_{FE}	132	-	189	-
Current Gain Group	L M N O P	h_{FE} h_{FE} h_{FE} h_{FE} h_{FE}	170 213 263 333	- 300 370 476	- - - -
Collector Base Breakdown Voltage at $I_C = 10 \mu\text{A}$	$V_{(BR)CBO}$	30	-	-	V
Collector Emitter Breakdown Voltage at $I_C = 10 \text{ mA}$	$V_{(BR)CEO}$	25	-	-	V
Emitter Base Breakdown Voltage at $I_E = 100 \mu\text{A}$	$V_{(BR)EBO}$	5	-	-	V
Collector Cutoff Current at $V_{CB} = 20 \text{ V}$	I_{CBO}	-	-	0.1	μA
Emitter Cutoff Current at $V_{EB} = 5 \text{ V}$	I_{EBO}	-	-	0.5	μA
Collector Saturation Voltage at $I_C = 500 \text{ mA}$, $I_B = 50 \text{ mA}$	$V_{CE(sat)}$	-	-	0.7	V
Gain Bandwidth Product at $V_{CE} = 5 \text{ V}$, $I_C = 10 \text{ mA}$	f_T	-	100	-	MHz
Output Capacitance at $V_{CB} = 5 \text{ V}$, $f = 1 \text{ MHz}$	C_{OB}	-	12	-	pF



SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



ISO/TS 16949 : 2002
Certificate No. 05103



ISO 14001:2004
Certificate No. 7116



ISO 9001:2000
Certificate No. 0506098

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